

SCHOTTKY DIE SPECIFICATION

TYPE: MBR1100S

General Description: 100 V 1 A (Low Ir)

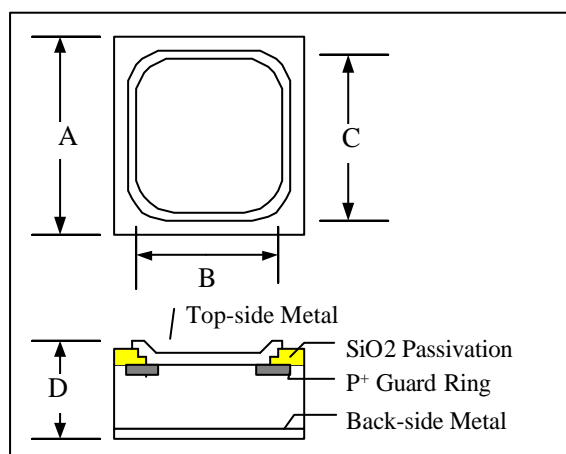
Single Anode

ELECTRICAL CHARACTERISTICS	SYM	Spec. Limit	Die Sort	UNIT
DC Blocking Voltage: Ir=1mA(for wafer form)	VRRM	100	105	Volt
Ir=0.5mA (for dice form)				
Average Rectified Forward Current	IFAV	1		Amp
Maximum Instantaneous Forward Voltage				
@ 1 Amperes, Ta=25°C	VF MAX	0.85	0.84	Volt
Maximum Instantaneous Reverse Voltage				
VR= 100 Volt, Ta=25°C	IR MAX	0.05	0.045	mA
Maximum Junction Capacitance @ 0V, 1MHZ	Cj MAX			pF
MAXIMUM RATINGS				
Nonrepetitive Peak Surge Current	IFSM	25		Amp
Operating Junction Temperature	Tj	-65 to +125		°C
Storage Temperatures	TSTG	-65 to +125		°C

Specification apply to die only. Actual performance may degrade when assembled.

MEMT does not guarantee device performance after assembly.

Data sheet information is subjected to change without notice.

DICE OUTLINE DRAWING


DIM	ITEM	um ²	Mil ²
A	Die Size	914	35.98
B	Top Metal Pad Size	814	32.0
C	Passivation Seal	834	32.8
D	Thickness (Min)	254	10
	Thickness (Max)	305	12

PS:

(1)Cutting street width is around 80um(3.14mil).

(2)Both of top-side and back-side metals are Ti/Ni/Ag.